[redacted]

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	140	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	85	
I_{DM}	Pulsed Drain Current		

[redacted]

Symbol	Characteristics	Typ.	Max.	Units
	Junction-to-case			

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	100			V	V_{GS} = 0V, I_D
$R_{DS(on)}$	Static Drain-to-Source on-resistance		4.4	6	m	V_{GS}=10V, I_D=20A
$V_{GS(th)}$	Gate threshold voltage	2		4	V	V_{DS}=V_{GS},I_D=250uA
I_{DSS}	Drain-to-Source leakage current T_j=25°C			1		V_{DS}=100V,V_{GS}=0V,
I_{GSS}	Gate-to-Source forward leakage			100	nA	V_{GS}=20V,V_{DS}=0V
				-100		V_{GS}=-20V,V_{DS}=0V
Q_g	Total gate charge		43		nC	T_j=25°C, V_{GS}=10V, V_{DS}=50V,I_D=20A
Q_{gs}	Gate-to-Source charge		10			
Q_{gd}	Gate-to-Drain("Miller") charge		11			
$t_{d(on)}$	Turn-on delay time		13		ns	V_{GS}=10V V_{DS}=50V R_G=3 I_D=20A
t_r	Rise time		26			
$t_{d(off)}$	Turn-Off delay time		45			
t_f	Fall time		38			
C_{iss}	Input capacitance		3880		pF	V_{GS}=0V V_{DS}=50V f=100kHz
C_{oss}	Output capacitance		572			
C_{rss}	Reverse transfer capacitance		17			

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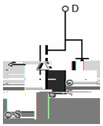
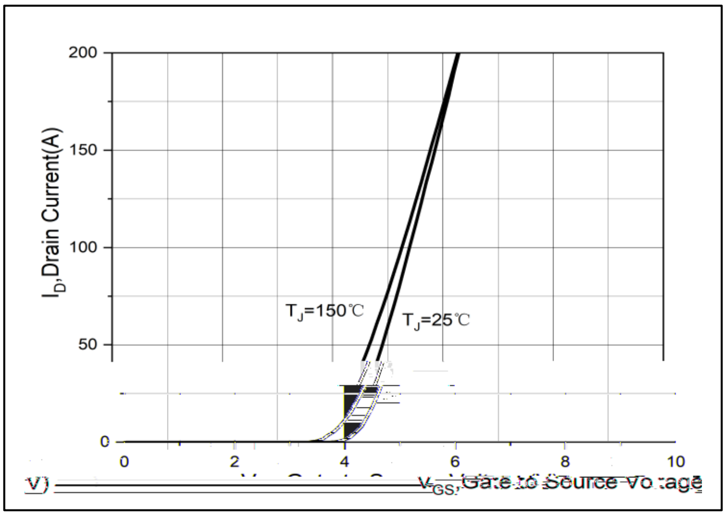
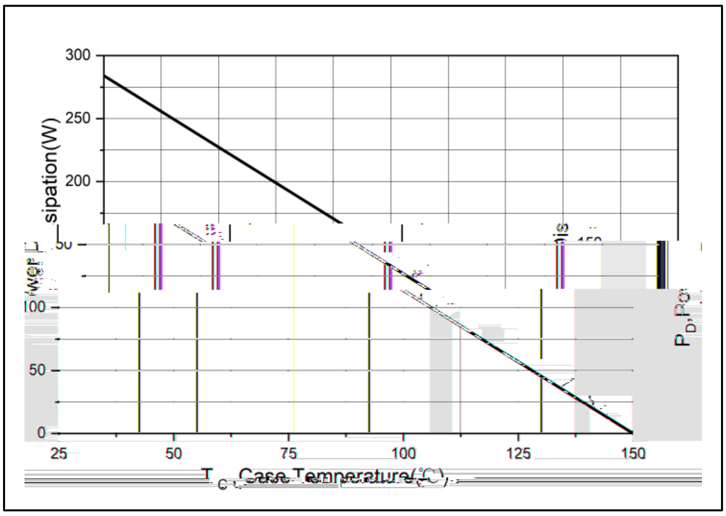
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)			167	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)			417	A	
V_{SD}	Diode Forward Voltage			1.2	V	I_S=20A, V_{GS}=0V
trr	Reverse Recovery Time		60		ns	I_F=20A, di/dt=1
Qrr	Reverse Recovery Charge		61		nC	

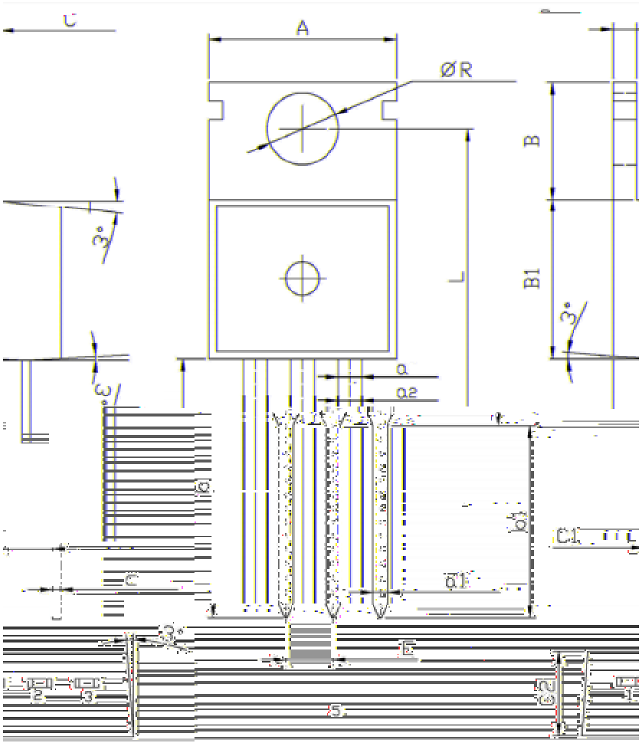
[redacted]

Typical Electrical and Thermal Characteristics





Unit:mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	9.8	10.2	C	1.2	1.4
R	3.56	3.64	B	6.3	6.7
L	15.7	16.1	B1	9.0	9.4
b	12.6	13.6	C1	2.2	2.6
b1	9.6	10.6	a1	0.7	0.9
a	1.22	1.32	c	0.4	0.6
E	2.34	2.74	C2	4.3	4.7
a2	1.25	1.45			

[redacted]

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mMli08869 0 55.2 8474W*nBTy12( )11(H)-10(o)23(w)-121(t)11(o)2-54( )11(a)23(n)23(y)-32( )11(a)23(n)23(d)23( )-54(a)23(l)22(l)2